L Number	Hits	Search Text	DB	Time stamp
155	2447	@ad<=20030922 and (257/750-752).ccls.	USPAT; US-PGPUB;	2004/11/01 09:03
156	1757	@ad<=20030922 and (257/753-756).ccls.	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/11/01 09:05
157	3767	@ad<=20030922 and (257/757-760).ccls.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/11/01 09:06
160	1886	@ad<=20030922 and (257/773).ccls.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/11/01 09:07
161	126	<pre>@ad&lt;=20030922 and 'dielectric constant' with 'SiOC'</pre>	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/11/01 09:15
165	7	<pre>@ad&lt;=20030922 and 'conductive plug' with 'Cu' with 'W' with 'silicide'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/11/01 09:31
166	138	<pre>@ad&lt;=20030922 and 'conductive' with 'Cu' with 'W' with 'silicide'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/11/01 09:18
167	1	<pre>@ad&lt;=20030922 and 'interconnect' same 'conductive' with 'Cu' with 'W' with 'silicide'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/11/01
168	12	<pre>@ad&lt;=20030922 and 'interconnection' same 'conductive' with 'Cu' with 'W' with 'silicide'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/11/01 09:19
169	36	<pre>@ad&lt;=20030922 and 'interconnection' same 'substrate' with 'Silicon' with 'silicon germanium'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/11/01 09:32
-	1705	@ad<=20020607 and (257/773).ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/27
_	4488	@ad<=20020607 and (438/622-624).ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/11/01 09:09
-	557	@ad<=20020607 and (438/629).ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/27
-	1623	@ad<=20020607 and (438/637).ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/27

Search History 11/1/04 10:26:26 AM Page 1

1		<u> </u>		
	545	@ad<=20020607 and (438/631).ccls.	USPAT; 2004/04/27 US-PGPUB; 11:42 EPO; JPO; DERWENT;	
			IBM TDB	
-	0	@ad<=20020607 and 'interconnection' and	USPAT; 2004/10/31	
		'IDL' with 'SiOC' and 'insulating' with	US-PGPUB; 08:22	
		'SiC'	EPO; JPO;	
			DERWENT;	
<b>,</b>	_ '	<u> </u>	IBM_TDB	
-	0	@ad<=20020607 and 'interconnection' and	USPAT; 2003/12/10	
		'IDL' same 'SiOC' with 'SiC'	US-PGPUB; 10:43 EPO; JPO;	
			DERWENT;	
1			IBM TDB	
-	0	@ad<=20020607 and 'interconnection' and	USPĀT; 2003/12/10	
		'SiOC' same 'SiC' same 'USG'	US-PGPUB; 10:43	ĺ
			EPO; JPO;	
}			DERWENT;	
_	23	  @ad<=20020607 and 'interconnection' and	IBM_TDB USPAT; 2004/10/31	
	23	'SiOC' same 'SiC'	US-PGPUB; 08:34	
]			EPO; JPO;	
			DERWENT;	
]		<u> </u>	IBM_TDB	ł
-	1	@ad<=20020607 and 'dielectric' same	USPAT; 2003/12/10	ŀ
		'SiOC' same 'undoped silicate'	US-PGPUB; 10:50 EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	28	@ad<=20020607 and 'dielectric' same	USPAT; 2004/04/27	
]	,	'SiOC' same 'SiC'	US-PGPUB; 09:57	
			EPO; JPO;	
			DERWENT;	
	2	   @ad<=20020607 and 'dielectric' same	IBM_TDB USPAT; 2003/12/10	
-	2	'SiOC' same 'SiC' same 'PSG'	US-PGPUB;   12:12	
		Side Same Sie Same 150	EPO; JPO;	
			DERWENT;	
	•		IBM_TDB	
-	1	@ad<=20020607 and 'dielectric' same	USPAT; 2003/12/10	
		'SiOC' same 'SiC' same 'USG'	US-PGPUB; 12:13	
] ]			EPO; JPO; DERWENT;	
1			IBM TDB	
] -	0	@ad<=20020607 and 'interconnection' and	USPAT; 2004/04/26	
1		'SiOC' same 'USG' same 'SiN'	US-PGPUB; 17:40	
			EPO; JPO;	
1			DERWENT;	
]_	26	   @ad<=20020607 and 'interconnection' and	IBM_TDB USPAT; 2004/04/26	
	20	'SiOC' same 'SiC'	US-PGPUB; 17:39	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	@ad<=20020607 and 'interconnection' and	USPAT; 2004/04/26	
		'SiOC' and 'USG' and 'SiN'	US-PGPUB; 17:45 EPO; JPO;	
			DERWENT;	
			IBM TDB	
	15	@ad<=20020607 and 'interconnection' and	USPAT; 2004/04/26	
		'SiOC' same 'SiC' and 'SiN'	US-PGPUB; 17:45	
			EPO; JPO;	
			DERWENT;	
_	28	   @ad<=20020607 and 'low k' same 'silicon	IBM_TDB   2004/09/09	ŀ
	20	oxide' same 'SiN'	US-PGPUB; 14:34	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	

- 969 @ad<=20020607 and (257/750).ccls. USPAT; 2004/04 US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; 2004/04 US-PGPUB; EPO; JPO; DERWENT; ISM TDB USPAT; 11:44 EPO; JPO; DERWENT; IBM TDB USPAT; 11:44 EPO; JPO; DERWENT; IBM TDB USPAT; 2004/04 USPAT; 2004/04	
EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	/27
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	/27
- 2856 @ad<=20020607 and (257/758-760).ccls.   IBM_TDB	/27
- 2856 @ad<=20020607 and (257/758-760).ccls. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	/27
US-PGPUB; 11:44 EPO; JPO; DERWENT; IBM TDB	, - ·
EPO; JPO; DERWENT; IBM TDB	
IBM TDB	
1 1737   Made=20020607 and /257/772\ acia   trenam.   2004/04	
	/27
US-PGPUB;   11:45	
EPO; JPO;	
DERWENT;	
IBM_TDB	/27
US-PGPUB; 11:47	/2/
EPO; JPO;	
DERWENT;	
IBM TDB	
- 564 @ad<=20020607 and (438/629).ccls. USPAT; 2004/04	/27
US-PGPUB; 11:47	
EPO; JPO;	
DERWENT;	
IBM_TDB	
- 1664 @ad<=20020607 and (438/637).ccls. USPAT; 2004/04	/27
US-PGPUB; 11:49	
EPO; JPO;	
DERWENT;	
	/27
- 548 @ad<=20020607 and (438/631).ccls. USPAT; 2004/04 US-PGPUB; 11:49	/2/
EPO; JPO;	
DERWENT;	
IBM TDB	
- 2 "20030227087" USPAT; 2004/09	/09
US-PGPUB; 13:41	
EPO; JPO;	
DERWENT;	
IBM_TDB	
- 86 @ad<=20020607 and 'hard mask' same 'SiN' USPAT; 2004/09	/10
with 'oxide' US-PGPUB; 12:22	
EPO; JPO;	
DERWENT;	
	/09
with 'SiC' US-PGPUB; 14:36	, 55
EPO; JPO;	
DERWENT;	
IBM TDB	
- 18 @ad<=20020607 and 'low k' same 'hard USPAT; 2004/09	/09
mask' same 'SiN' with 'SiC' US-PGPUB; 14:36	
EPO; JPO;	
DERWENT;	
IBM_TDB	(0.0
- 2 @ad<=20020607 and 'MSQ' same 'hard mask' USPAT; 2004/10	/31
same 'SiN' with 'SiC' US-PGPUB; 08:43	
EPO; JPO;	
DERWENT;   IBM TDB	1
- 5 @ad<=20020607 and 'MSQ' same 'SiN' with USPAT; 2004/09	/09
'SiC' US-PGPUB; 14:59	, 👣
EPO; JPO;	
DERWENT;	
IBM TDB	
- 19 @ad<=20020607 and 'hard mask' same 'SiC' USPAT; 2004/09	/10
with 'oxide' US-PGPUB; 12:23	
EPO; JPO;	
DERWENT;	
IBM TDB	

				_
_	2	<pre>@ad&lt;=20020607 and 'hard mask' same 'SiC' with 'TEOS'</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/10 13:41
			IBM_TDB	
-	17	<pre>@ad&lt;=20020607 and 'etch stop' with 'SiC' with 'SiO.sub.2'</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/10
	2	<pre>@ad&lt;=20020607 and 'MSQ' same 'etch stop' with 'SiC' with 'SiO.sub.2'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/09/10
_	4	"6677183"	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/09/10 15:38
-	649	@ad<=20020607 and 'interconnection' same 'tungsten' with 'copper' same' low k' same 'etch stop' with 'SiC'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/31 08:25
	31	<pre>@ad&lt;=20020607 and 'interconnection' same 'tungsten plug' with 'copper' same' low k' same 'etch stop' with 'SiC' same 'USG'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/31 08:30
-	90	@ad<=20020607 and 'tungsten copper' same 'interconnection'	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/10/31 08:32
-	0	<pre>@ad&lt;=20020607 and 'tungsten copper' same 'interconnection' and 'low k' and 'SiC'</pre>	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/31 08:32
_	17	@ad<=20020607 and 'tungsten copper' same 'interconnection' and 'etch stop'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/31 08:32
-	0	@ad<=20020607 and 'interconnection' and 'USG' same 'SiC' same 'low k'	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/10/31 08:35
-	7	<pre>@ad&lt;=20020607 and 'interconnection' and 'USG' and 'SiC' and 'low k'</pre>	DERWENT; IBM_TDB USPAT; US-PGPUB;	2004/10/31 08:35
_	, 12	@ad<=20030922 and 'interconnection' and	EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/10/31
		'USG' and 'SiC' and 'low k'	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	08:35
-	. 1	"6312793".PN.	USPĀT	2004/10/31
-	1	"6303523".PN.	USPAT	2004/10/31
-	1	"6238751".PN.	USPAT	2004/10/31
-	1	"6147009".PN.	USPAT	2004/10/31
-	1	"6072227".PN.	USPAT	2004/10/31
-	1	"6054379".PN.	USPAT	2004/10/31
L	I	<u> </u>	<u> </u>	,

	1	"6001747".PN.	USPAT	2004/10/31
	_			08:41
_	1	"5989998".PN.	USPAT	2004/10/31
	1		<b> </b>	08:41
_	2	@ad<=20020607 and 'USG' same 'hard mask'	USPAT;	2004/10/31
		same 'low dielectric'	US-PGPUB;	08:46
			EPO; JPO;	
		,	DERWENT;	
			IBM TDB	
-	270	@ad<=20020607 and 'dielectric' same 'hard	USPĀT;	2004/10/31
	+	mask' same 'low dielectric'	US-PGPUB;	08:58
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	24	T	USPAT;	2004/10/31
		'dielectric' same 'hard mask' same 'low	US-PGPUB;	08:53
	1	dielectric'	EPO; JPO;	,
			DERWENT;	
			IBM_TDB	
-	4	(("6465867") or ("6016000")).PN.	USPAT;	2004/10/31
			US-PGPUB;	08:55
	1		EPO; JPO;	
			DERWENT;	
•			IBM_TDB	
-	2	"20010045651"	USPAT;	2004/10/31
			US-PGPUB;	08:55
			EPO; JPO;	,
			DERWENT;	
	1	<u> </u>	IBM_TDB	
-	190	• · · ·   = · · = · · · · · · · · · · · ·	USPAT;	2004/10/31
•	1	same 'low dielectric'	US-PGPUB;	08:59
		'	EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/11/01
-	56	•••• ••• ••• ••• ••• ••• ••• ••• •••	USPAT;	2004/11/01
		same 'low dielectric' same 'barrier'	US-PGPUB;	07:19
	,		EPO; JPO;	
	1		DERWENT;	
	]	0-4-20020607 and 14:-1	IBM_TDB	2004/10/21
-	34	•	USPAT;	2004/10/31 08:59
		same 'low-k' same 'barrier'	US-PGPUB; EPO; JPO;	00:39
			DERWENT;	
	į	1	IBM TDB	